

## Low-Voltage, Single Supply, Dual SPST, SPDT Analog Switches

The Intersil ISL5120–ISL5123 devices are precision, bidirectional, dual analog switches designed to operate from a single +2.7V to +12V supply. Targeted applications include battery powered equipment that benefit from the devices' low power consumption (5 $\mu$ W), low leakage currents (100pA max), and fast switching speeds ( $t_{ON}$  = 28ns,  $t_{OFF}$  = 20ns). Cell phones, for example, often face ASIC functionality limitations. The number of analog input or GPIO pins may be limited and digital geometries are not well suited to analog switch performance. This family of parts may be used to “mux-in” additional functionality while reducing ASIC design risk. Some of the smallest packages are available, alleviating board space limitations, and making Intersil's newest line of low-voltage switches an ideal solution.

The ISL5120/ISL5121/ISL5122 are dual single-pole/single-throw (SPST) devices. The ISL5120 has two normally open (NO) switches; the ISL5121 has two normally closed (NC) switches; the ISL5122 has one NO and one NC switch and can be used as an SPDT. The ISL5123 is a committed SPDT, which is perfect for use in 2-to-1 multiplexer applications.

**TABLE 1. SUMMARY OF FEATURES**

	ISL5120	ISL5121	ISL5122	ISL5123
<b>Number of Switches</b>	2	2	2	1
<b>SW 1 / SW 2</b>	NO / NO	NC / NC	NO / NC	SPDT
<b>3.3V <math>R_{ON}</math></b>	32 $\Omega$	32 $\Omega$	32 $\Omega$	32 $\Omega$
<b>3.3V <math>t_{ON}</math> / <math>t_{OFF}</math></b>	40ns / 20ns	40ns / 20ns	40ns / 20ns	40ns / 20ns
<b>5V <math>R_{ON}</math></b>	19 $\Omega$	19 $\Omega$	19 $\Omega$	19 $\Omega$
<b>5V <math>t_{ON}</math> / <math>t_{OFF}</math></b>	28ns / 20ns	28ns / 20ns	28ns / 20ns	28ns / 20ns
<b>12V <math>R_{ON}</math></b>	11 $\Omega$	11 $\Omega$	11 $\Omega$	11 $\Omega$
<b>12V <math>t_{ON}</math> / <math>t_{OFF}</math></b>	25ns / 17ns	25ns / 17ns	25ns / 17ns	25ns / 17ns
<b>Packages</b>	8 Ld SOIC, 8 Ld SOT-23			8 Ld SOIC, 6 Ld SOT-23

## Related Literature

- Technical Brief TB363 “Guidelines for Handling and Processing Moisture Sensitive Surface Mount Devices (SMDs)”

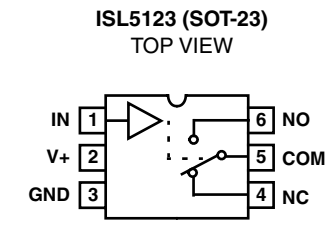
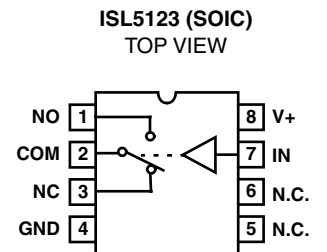
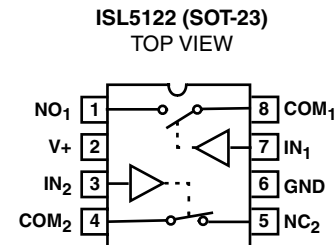
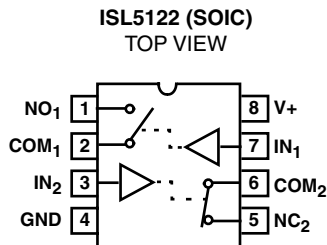
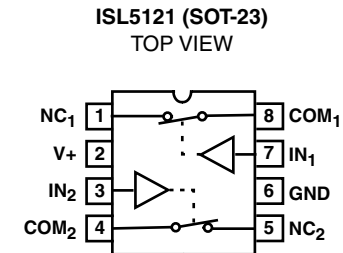
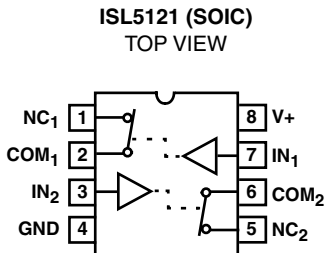
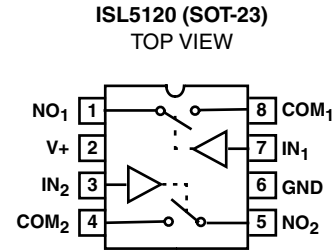
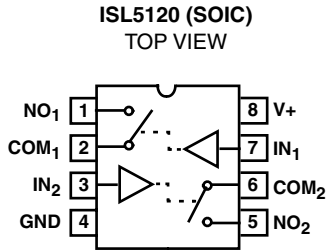
## Features

- Improved (lower  $R_{ON}$ , faster switching), pin compatible replacements for ISL84541–44
- Fully specified at 3.3V, 5V, and 12V supplies
- ON resistance ( $R_{ON}$ ) . . . . . 19 $\Omega$
- $R_{ON}$  matching between channels . . . . . <1 $\Omega$
- Low charge injection . . . . . 5pC (Max)
- Single supply operation. . . . . +2.7V to +12V
- Low power consumption ( $P_D$ ). . . . . <5 $\mu$ W
- Low leakage current. . . . . 10nA
- Fast switching action
  - $t_{ON}$  . . . . . 28ns
  - $t_{OFF}$  . . . . . 20ns
- Guaranteed break-before-make (ISL5122/ISL5123 only)
- Minimum 2000V ESD protection per method 3015.7
- TTL, CMOS compatible
- Available in SOT-23 packaging

## Applications

- Battery powered, handheld, and portable equipment
  - Cellular/mobile phones
  - Pagers
  - Laptops, notebooks, palmtops
- Communications systems
  - Military radios
  - PBX, PABX
- Test equipment
  - Ultrasound
  - Electrocardiograph
- Heads-up displays
- Audio and video switching
- Various circuits
  - +3V/+5V DACs and ADCs
  - Sample and hold circuits
  - Digital filters
  - Operational amplifier gain switching networks
  - High frequency analog switching
  - High speed multiplexing
  - Integrator reset circuits

**Pinouts** (Note 1)



NOTE:

1. Switches Shown for Logic "0" Input.

**Truth Table**

LOGIC	ISL5120	ISL5121	ISL5122		ISL5123	
	SW 1,2	SW 1,2	SW 1	SW 2	PIN NC	PIN NO
0	OFF	ON	OFF	ON	ON	OFF
1	ON	OFF	ON	OFF	OFF	ON

NOTE: Logic "0"  $\leq 0.8V$ . Logic "1"  $\geq 2.4V$ .

**Pin Descriptions**

PIN	FUNCTION
V+	System Power Supply Input (+2.7V to +12V)
GND	Ground Connection
IN	Digital Control Input
COM	Analog Switch Common Pin
NO	Analog Switch Normally Open Pin
NC	Analog Switch Normally Closed Pin
N.C.	No Internal Connection

## Ordering Information

PART NO. (BRAND) (NOTE 2)	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
ISL5120CB	0 to 70	8 Ld SOIC	M8.15
ISL5120IB	-40 to 85	8 Ld SOIC	M8.15
ISL5120CH-T (120C)	0 to 70	8 Ld SOT-23 (Note 3)	P8.064
ISL5120IH-T (120I)	-40 to 85	8 Ld SOT-23 (Note 3)	P8.064
ISL5121CB	0 to 70	8 Ld SOIC	M8.15
ISL5121IB	-40 to 85	8 Ld SOIC	M8.15
ISL5121CH-T (121C)	0 to 70	8 Ld SOT-23 (Note 3)	P8.064
ISL5121IH-T (121I)	-40 to 85	8 Ld SOT-23 (Note 3)	P8.064
ISL5122CB	0 to 70	8 Ld SOIC	M8.15
ISL5122IB	-40 to 85	8 Ld SOIC	M8.15
ISL5122CH-T (122C)	0 to 70	8 Ld SOT-23 (Note 3)	P8.064
ISL5122IH-T (122I)	-40 to 85	8 Ld SOT-23 (Note 3)	P8.064
ISL5123CB	0 to 70	8 Ld SOIC	M8.15
ISL5123IB	-40 to 85	8 Ld SOIC	M8.15
ISL5123CH-T (123C)	0 to 70	6 Ld SOT-23 (Note 3)	P6.064
ISL5123IH-T (123I)	-40 to 85	6 Ld SOT-23 (Note 3)	P6.064

NOTES:

2. Most surface mount devices are available on tape and reel; add “-T” to suffix.
3. Product in Development.

# ISL5120, ISL5121, ISL5122, ISL5123

## Absolute Maximum Ratings

V+ to GND	-0.3 to 15V
Input Voltages	
IN (Note 4)	-0.3 to ((V+) + 0.3V)
NO, NC (Note 4)	-0.3 to ((V+) + 0.3V)
Output Voltages	
COM (Note 4)	-0.3 to ((V+) + 0.3V)
Continuous Current (Any Terminal)	30mA
Peak Current NO, NC, or COM (Pulsed 1ms, 10% Duty Cycle, Max)	40mA
ESD Rating (Per MIL-STD-883 Method 3015)	>2kV

## Thermal Information

Thermal Resistance (Typical, Note 5)	$\theta_{JA}$ (°C/W)
6 Ld SOT-23 Package	230
8 Ld SOT-23 Package	215
8 Ld SOIC Package	170
Maximum Junction Temperature (Plastic Package)	150°C
Moisture Sensitivity (See Technical Brief TB363) All Packages	Level 1
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) (Lead Tips Only)	300°C

## Operating Conditions

Temperature Range	
ISL512XCX	0°C to 70°C
ISL512XIX	-40°C to 85°C

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### NOTES:

- Signals on NC, NO, COM, or IN exceeding V+ or GND are clamped by internal diodes. Limit forward diode current to maximum current ratings.
- $\theta_{JA}$  is measured with the component mounted on a low effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

## Electrical Specifications - 5V Supply

Test Conditions: V+ = +4.5V to +5.5V, GND = 0V, V<sub>INH</sub> = 2.4V, V<sub>INL</sub> = 0.8V (Note 6), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 7) MIN	TYP	(NOTE 7) MAX	UNITS
<b>ANALOG SWITCH CHARACTERISTICS</b>						
Analog Signal Range, V <sub>ANALOG</sub>		Full	0	-	V+	V
ON Resistance, R <sub>ON</sub>	V+ = 4.5V, I <sub>COM</sub> = 1.0mA, V <sub>NO</sub> or V <sub>NC</sub> = 3.5V, See Figure 5	25	-	19	30	Ω
		Full	-	23	40	Ω
R <sub>ON</sub> Matching Between Channels, ΔR <sub>ON</sub>	V+ = 5V, I <sub>COM</sub> = 1.0mA, V <sub>NO</sub> or V <sub>NC</sub> = 3.5V	25	-	0.8	2	Ω
		Full	-	1	4	Ω
R <sub>ON</sub> Flatness, R <sub>FLAT(ON)</sub>	V+ = 5V, I <sub>COM</sub> = 1.0mA, V <sub>NO</sub> or V <sub>NC</sub> = 1V, 2V, 3V	Full	-	7	8	Ω
NO or NC OFF Leakage Current, I <sub>NO(OFF)</sub> or I <sub>NC(OFF)</sub>	V+ = 5.5V, V <sub>COM</sub> = 1V, 4.5V, V <sub>NO</sub> or V <sub>NC</sub> = 4.5V, 1V, Note 8	25	-0.1	0.01	0.1	nA
		Full	-5	-	5	nA
COM OFF Leakage Current, I <sub>COM(OFF)</sub>	V+ = 5.5V, V <sub>COM</sub> = 4.5V, 1V, V <sub>NO</sub> or V <sub>NC</sub> = 1V, 4.5V, Note 8	25	-0.1	-	0.1	nA
		Full	-5	-	5	nA
COM ON Leakage Current, I <sub>COM(ON)</sub>	V+ = 5.5V, V <sub>COM</sub> = 1V, 4.5V, or V <sub>NO</sub> or V <sub>NC</sub> = 1V, 4.5V, or Floating, Note 8	25	-0.2	-	0.2	nA
		Full	-10	-	10	nA
<b>DYNAMIC CHARACTERISTICS</b>						
Turn-ON Time, t <sub>ON</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 3V, R <sub>L</sub> = 1kΩ, C <sub>L</sub> = 35pF, V <sub>IN</sub> = 0 to 3V, See Figure 1	25	-	28	75	ns
		Full	-	40	150	ns
Turn-OFF Time, t <sub>OFF</sub>	V <sub>NO</sub> or V <sub>NC</sub> = 3V, R <sub>L</sub> = 1kΩ, C <sub>L</sub> = 35pF, V <sub>IN</sub> = 0 to 3V, See Figure 1	25	-	20	50	ns
		Full	-	30	100	ns
Break-Before-Make Time Delay (ISL5122, ISL5123), t <sub>D</sub>	R <sub>L</sub> = 300Ω, C <sub>L</sub> = 35pF, V <sub>NO</sub> = V <sub>NC</sub> = 3V, V <sub>IN</sub> = 0 to 3V, See Figure 3	Full	3	10	-	ns
Charge Injection, Q	C <sub>L</sub> = 1.0nF, V <sub>G</sub> = 0V, R <sub>G</sub> = 0Ω, See Figure 2	25	-	3	5	pC
OFF Isolation	R <sub>L</sub> = 50Ω, C <sub>L</sub> = 5pF, f = 1MHz, See Figure 4	25	-	76	-	dB
Crosstalk (Channel-to-Channel)	R <sub>L</sub> = 50Ω, C <sub>L</sub> = 5pF, f = 1MHz, See Figure 6	25	-	-105	-	dB
Power Supply Rejection Ratio	R <sub>L</sub> = 50Ω, C <sub>L</sub> = 5pF, f = 1MHz	25	-	60	-	dB
NO or NC OFF Capacitance, C <sub>OFF</sub>	f = 1MHz, V <sub>NO</sub> or V <sub>NC</sub> = V <sub>COM</sub> = 0V, See Figure 7	25	-	8	-	pF
COM OFF Capacitance, C <sub>COM(OFF)</sub>	f = 1MHz, V <sub>NO</sub> or V <sub>NC</sub> = V <sub>COM</sub> = 0V, See Figure 7	25	-	8	-	pF

## ISL5120, ISL5121, ISL5122, ISL5123

### Electrical Specifications - 5V Supply

Test Conditions:  $V_+ = +4.5V$  to  $+5.5V$ ,  $GND = 0V$ ,  $V_{INH} = 2.4V$ ,  $V_{INL} = 0.8V$  (Note 6), Unless Otherwise Specified **(Continued)**

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 7) MIN	TYP	(NOTE 7) MAX	UNITS
COM ON Capacitance, $C_{COM(ON)}$	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$ , See Figure 7, ISL5120/1/2	25	-	21	-	pF
	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$ , See Figure 7, ISL5123	25	-	28	-	pF
<b>POWER SUPPLY CHARACTERISTICS</b>						
Power Supply Range		Full	2.7		12	V
Positive Supply Current, $I_+$	$V_+ = 5.5V$ , $V_{IN} = 0V$ or $V_+$ , all channels on or off	Full	-1	0.0001	1	$\mu A$
<b>DIGITAL INPUT CHARACTERISTICS</b>						
Input Voltage Low, $V_{INL}$		Full	-	-	0.8	V
Input Voltage High, $V_{INH}$		Full	2.4	-	-	V

**NOTES:**

6.  $V_{IN}$  = input voltage to perform proper function.
7. The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
8. Leakage parameter is 100% tested at high temp, and guaranteed by correlation at 25°C.

### Electrical Specifications - 3.3V Supply

Test Conditions:  $V_+ = +3.0V$  to  $+3.6V$ ,  $GND = 0V$ ,  $V_{INH} = 2.4V$ ,  $V_{INL} = 0.8V$  (Note 6), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 7) MIN	TYP	(NOTE 7) MAX	UNITS
<b>ANALOG SWITCH CHARACTERISTICS</b>						
Analog Signal Range, $V_{ANALOG}$		Full	0	-	$V_+$	V
ON Resistance, $R_{ON}$	$V_+ = 3V$ , $I_{COM} = 1.0mA$ , $V_{NO}$ or $V_{NC} = 1.5V$	25	-	32	50	$\Omega$
		Full	-	40	60	$\Omega$
$R_{ON}$ Matching Between Channels, $\Delta R_{ON}$	$V_+ = 3.3V$ , $I_{COM} = 1.0mA$ , $V_{NO}$ or $V_{NC} = 1.5V$	25	-	0.8	2	$\Omega$
		Full	-	1	4	$\Omega$
$R_{ON}$ Flatness, $R_{FLAT(ON)}$	$V_+ = 3.3V$ , $I_{COM} = 1.0mA$ , $V_{NO}$ or $V_{NC} = 0.5V$ , 1V, 1.5V	25	-	6	8	$\Omega$
		Full	-	7	12	$\Omega$
NO or NC OFF Leakage Current, $I_{NO(OFF)}$ or $I_{NC(OFF)}$	$V_+ = 3.6V$ , $V_{COM} = 1V$ , 3V, $V_{NO}$ or $V_{NC} = 3V$ , 1V, Note 8	25	-0.1	0.01	0.1	nA
		Full	-5	-	5	nA
COM OFF Leakage Current, $I_{COM(OFF)}$	$V_+ = 3.6V$ , $V_{COM} = 3V$ , 1V, $V_{NO}$ or $V_{NC} = 1V$ , 3V, Note 8	25	-0.1	0.01	0.1	nA
		Full	-5	-	5	nA
COM ON Leakage Current, $I_{COM(ON)}$	$V_+ = 3.6V$ , $V_{COM} = 1V$ , 3V, or $V_{NO}$ or $V_{NC} = 1V$ , 3V, or floating, Note 8	25	-0.2	-	0.2	nA
		Full	-10	-	10	nA
<b>DYNAMIC CHARACTERISTICS</b>						
Turn-ON Time, $t_{ON}$	$V_{NO}$ or $V_{NC} = 1.5V$ , $R_L = 1k\Omega$ , $C_L = 35pF$ , $V_{IN} = 0$ to 3V	25	-	40	120	ns
		Full	-	60	200	ns
Turn-OFF Time, $t_{OFF}$	$V_{NO}$ or $V_{NC} = 1.5V$ , $R_L = 1k\Omega$ , $C_L = 35pF$ , $V_{IN} = 0$ to 3V	25	-	20	50	ns
		Full	-	30	120	ns
Break-Before-Make Time Delay (ISL5122, ISL5123), $t_D$	$R_L = 300\Omega$ , $C_L = 35pF$ , $V_{NO}$ or $V_{NC} = 1.5V$ , $V_{IN} = 0$ to 3V	Full	3	20	-	ns
Charge Injection, Q	$C_L = 1.0nF$ , $V_G = 0V$ , $R_G = 0\Omega$	25	-	1	5	pC
OFF Isolation	$R_L = 50\Omega$ , $C_L = 5pF$ , $f = 1MHz$	25	-	76	-	dB
Crosstalk (Channel-to-Channel)		25	-	-105	-	dB
Power Supply Rejection Ratio	$R_L = 50\Omega$ , $C_L = 5pF$ , $f = 1MHz$	25	-	56	-	dB
NO or NC OFF Capacitance, $C_{OFF}$	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$	25	-	8	-	pF
COM OFF Capacitance, $C_{COM(OFF)}$	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$	25	-	8	-	pF

**ISL5120, ISL5121, ISL5122, ISL5123**

**Electrical Specifications - 3.3V Supply**

Test Conditions:  $V_+ = +3.0V$  to  $+3.6V$ ,  $GND = 0V$ ,  $V_{INH} = 2.4V$ ,  $V_{INL} = 0.8V$  (Note 6), Unless Otherwise Specified **(Continued)**

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 7) MIN	TYP	(NOTE 7) MAX	UNITS
COM ON Capacitance, $C_{COM(ON)}$	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$ , ISL5120/1/2	25	-	21	-	pF
	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$ , ISL5123	25	-	28	-	pF
<b>POWER SUPPLY CHARACTERISTICS</b>						
Positive Supply Current, $I_+$	$V_+ = 3.6V$ , $V_{IN} = 0V$ or $V_+$ , all channels on or off	Full	-1	-	1	$\mu A$
<b>DIGITAL INPUT CHARACTERISTICS</b>						
Input Voltage Low, $V_{INL}$		Full	-	-	0.8	V
Input Voltage High, $V_{INH}$		Full	2.4	-	-	V
Input Current, $I_{INH}$ , $I_{INL}$	$V_+ = 3.6V$ , $V_{IN} = 0V$ or $V_+$	Full	-0.5	-	0.5	$\mu A$

**Electrical Specifications - 12V Supply**

Test Conditions:  $V_+ = +10.8V$  to  $+13V$ ,  $GND = 0V$ ,  $V_{INH} = 4V$ ,  $V_{INL} = 0.8V$  (Note 6), Unless Otherwise Specified

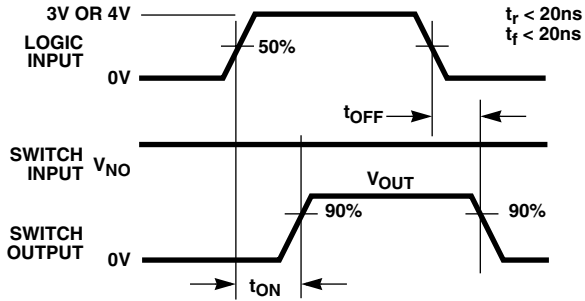
PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 7) MIN	TYP	(NOTE 7) MAX	UNITS
<b>ANALOG SWITCH CHARACTERISTICS</b>						
Analog Signal Range, $V_{ANALOG}$		Full	0	-	$V_+$	V
ON Resistance, $R_{ON}$	$V_+ = 10.8V$ , $I_{COM} = 1.0mA$ , $V_{NO}$ or $V_{NC} = 10V$	25	-	11	20	$\Omega$
		Full	-	15	25	$\Omega$
$R_{ON}$ Matching Between Channels, $\Delta R_{ON}$	$V_+ = 12V$ , $I_{COM} = 1.0mA$ , $V_{NO}$ or $V_{NC} = 10V$	25	-	0.8	2	$\Omega$
		Full	-	1	4	$\Omega$
$R_{ON}$ Flatness, $R_{FLAT(ON)}$	$V_+ = 12V$ , $I_{COM} = 1.0mA$ , $V_{NO}$ or $V_{NC} = 3V, 6V, 9V$	25	-	1	4	$\Omega$
		Full	-	-	6	$\Omega$
NO or NC OFF Leakage Current, $I_{NO(OFF)}$ or $I_{NC(OFF)}$	$V_+ = 13V$ , $V_{COM} = 1V, 12V$ , $V_{NO}$ or $V_{NC} = 12V, 1V$ , Note 8	25	-0.1	0.01	0.1	nA
		Full	-5	-	5	nA
COM OFF Leakage Current, $I_{COM(OFF)}$	$V_+ = 13V$ , $V_{COM} = 12V, 1V$ , $V_{NO}$ or $V_{NC} = 1V, 12V$ , Note 8	25	-0.1	0.01	0.1	nA
		Full	-5	-	5	nA
COM ON Leakage Current, $I_{COM(ON)}$	$V_+ = 13V$ , $V_{COM} = 1V, 12V$ , or $V_{NO}$ or $V_{NC} = 1V, 12V$ , or floating, Note 8	25	-0.2	-	0.2	nA
		Full	-10	-	10	nA
<b>DYNAMIC CHARACTERISTICS</b>						
Turn-ON Time, $t_{ON}$	$V_{NO}$ or $V_{NC} = 10V$ , $R_L = 1k\Omega$ , $C_L = 35pF$ , $V_{IN} = 0$ to $4V$	25	-	25	35	ns
		Full	-	35	55	ns
Turn-OFF Time, $t_{OFF}$	$V_{NO}$ or $V_{NC} = 10V$ , $R_L = 1k\Omega$ , $C_L = 35pF$ , $V_{IN} = 0$ to $4V$	25	-	17	30	ns
		Full	-	26	50	ns
Break-Before-Make Time Delay (ISL5122, ISL5123), $t_D$	$R_L = 300\Omega$ , $C_L = 35pF$ , $V_{NO}$ or $V_{NC} = 10V$ , $V_{IN} = 0$ to $4V$	Full	0	2		ns
Charge Injection, Q	$C_L = 1.0nF$ , $V_G = 0V$ , $R_G = 0\Omega$	25	-	5	15	pC
OFF Isolation	$R_L = 50\Omega$ , $C_L = 5pF$ , $f = 1MHz$	25	-	76	-	dB
Crosstalk (Channel-to-Channel)		25	-	-105	-	dB
Power Supply Rejection Ratio	$R_L = 50\Omega$ , $C_L = 5pF$ , $f = 1MHz$	25	-	63	-	dB
NO or NC OFF Capacitance, $C_{OFF}$	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$	25	-	8	-	pF
COM OFF Capacitance, $C_{COM(OFF)}$	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$	25	-	8	-	pF
COM ON Capacitance, $C_{COM(ON)}$	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$ , ISL5120/1/2	25	-	21	-	pF
	$f = 1MHz$ , $V_{NO}$ or $V_{NC} = V_{COM} = 0V$ , ISL5123	25	-	28	-	pF
<b>POWER SUPPLY CHARACTERISTICS</b>						
Positive Supply Current, $I_+$	$V_+ = 13V$ , $V_{IN} = 0V$ or $V_+$ , all channels on or off	Full	-1	-	1	$\mu A$
<b>DIGITAL INPUT CHARACTERISTICS</b>						
Input Voltage Low, $V_{INL}$		Full	-	-	0.8	V

Electrical Specifications - 12V Supply

Test Conditions:  $V_+ = +10.8V$  to  $+13V$ ,  $GND = 0V$ ,  $V_{INH} = 4V$ ,  $V_{INL} = 0.8V$  (Note 6), Unless Otherwise Specified (Continued)

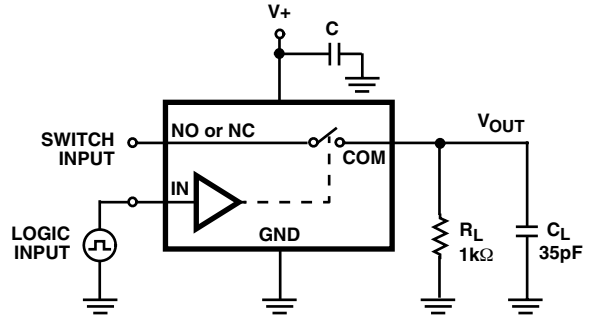
PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 7) MIN	TYP	(NOTE 7) MAX	UNITS
Input Voltage High, $V_{INH}$		Full	4	3	-	V
Input Current, $I_{INH}$ , $I_{INL}$	$V_+ = 13V$ , $V_{IN} = 0V$ or $V_+$	Full	-0.5	-	0.5	$\mu A$

Test Circuits and Waveforms



Logic input waveform is inverted for switches that have the opposite logic sense.

FIGURE 1A. MEASUREMENT POINTS



Repeat test for all switches.  $C_L$  includes fixture and stray capacitance.

$$V_{OUT} = V_{(NO \text{ or } NC)} \frac{R_L}{R_L + R_{(ON)}}$$

FIGURE 1B. TEST CIRCUIT

FIGURE 1. SWITCHING TIMES

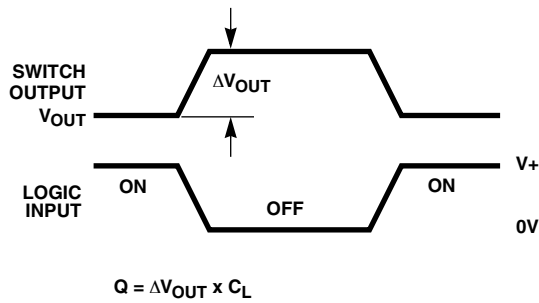


FIGURE 2A. MEASUREMENT POINTS

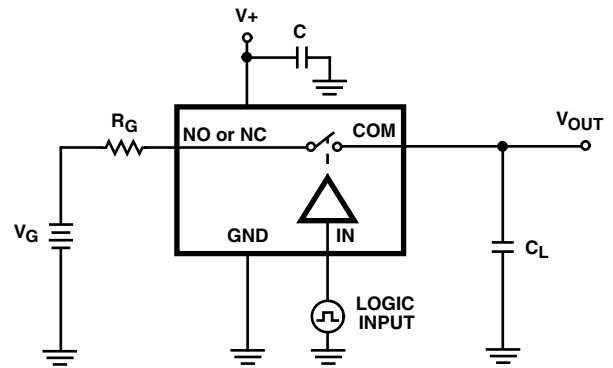


FIGURE 2B. TEST CIRCUIT

FIGURE 2. CHARGE INJECTION

Test Circuits and Waveforms (Continued)

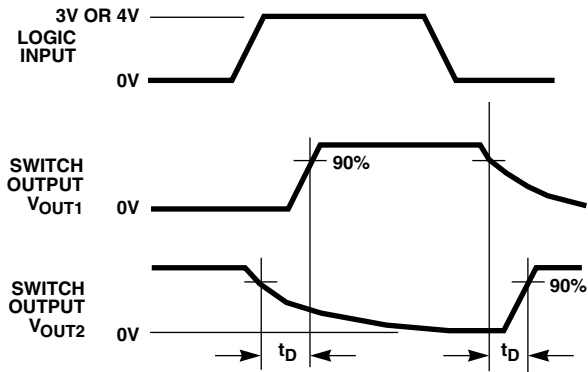
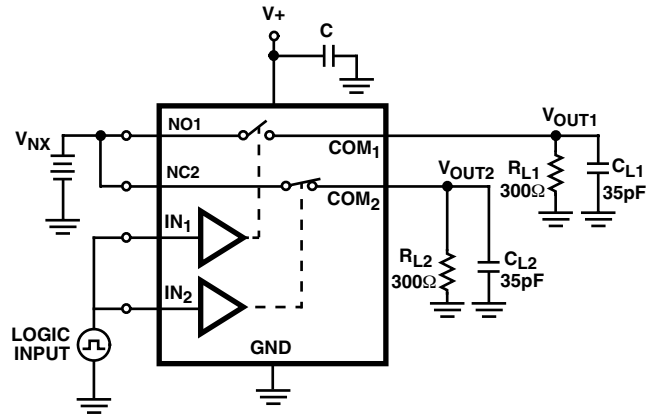


FIGURE 3A. MEASUREMENT POINTS (ISL5122 ONLY)



$C_L$  includes fixture and stray capacitance.

FIGURE 3B. TEST CIRCUIT (ISL5122 ONLY)

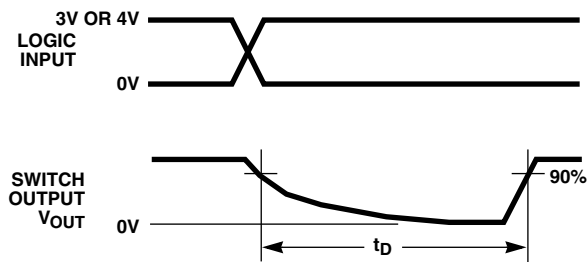
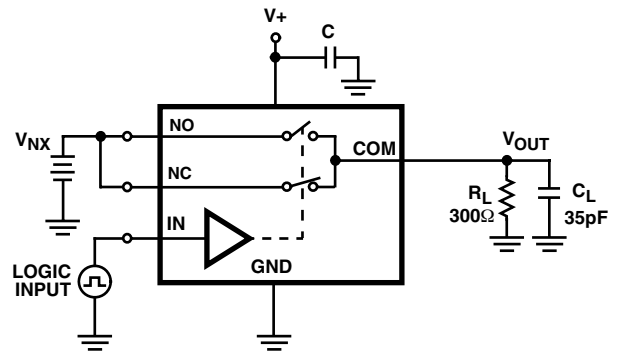


FIGURE 3C. MEASUREMENT POINTS (ISL5123 ONLY)



$C_L$  includes fixture and stray capacitance.

FIGURE 3D. TEST CIRCUIT (ISL5123 ONLY)

FIGURE 3. BREAK-BEFORE-MAKE TIME

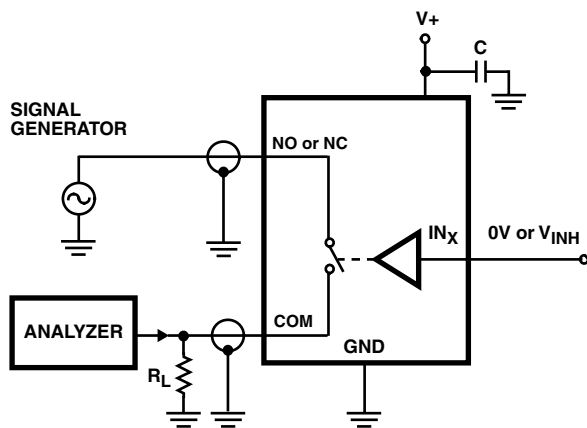


FIGURE 4. OFF ISOLATION TEST CIRCUIT

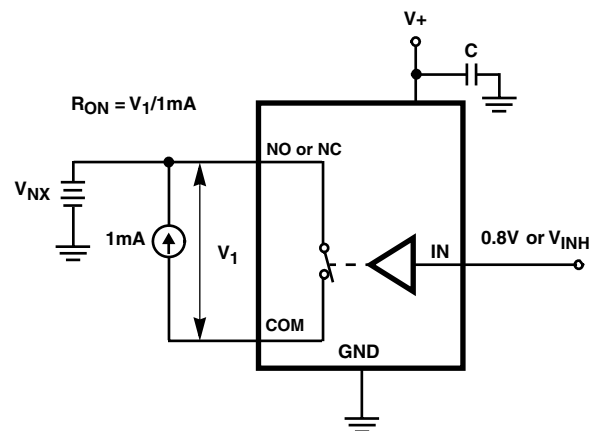


FIGURE 5.  $R_{ON}$  TEST CIRCUIT



Test Circuits and Waveforms (Continued)

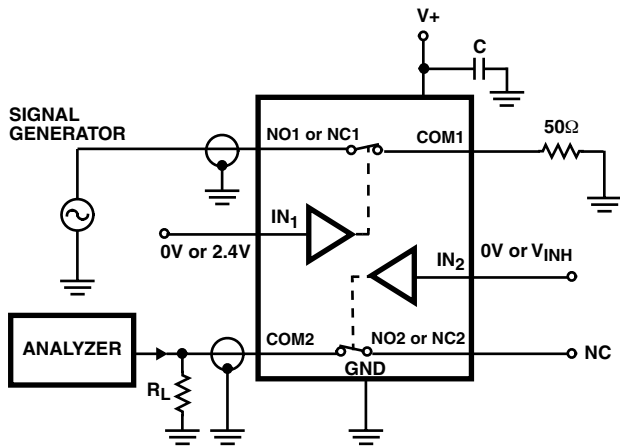


FIGURE 6. CROSSTALK TEST CIRCUIT

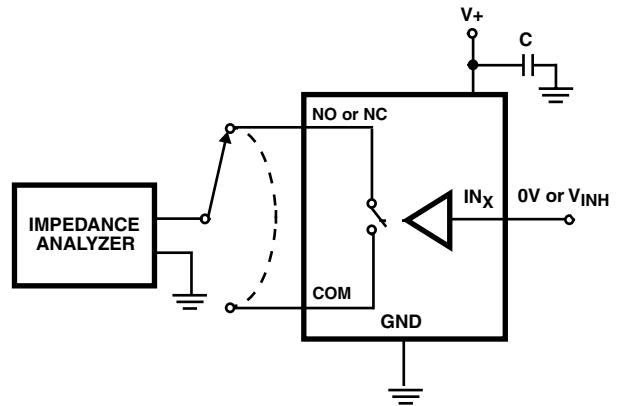


FIGURE 7. CAPACITANCE TEST CIRCUIT

## Detailed Description

The ISL5120–ISL5123 bidirectional, dual analog switches offer precise switching capability from a single 2.7V to 12V supply with low on-resistance ( $19\Omega$ ) and high speed operation ( $t_{ON} = 28\text{ns}$ ,  $t_{OFF} = 20\text{ns}$ ). The devices are especially well suited to portable battery powered equipment thanks to the low operating supply voltage (2.7V), low power consumption ( $5\mu\text{W}$ ), low leakage currents (100pA max), and the tiny SOT-23 packaging. High frequency applications also benefit from the wide bandwidth, and the very high off isolation and crosstalk rejection.

### Supply Sequencing And Overvoltage Protection

With any CMOS device, proper power supply sequencing is required to protect the device from excessive input currents which might permanently damage the IC. All I/O pins contain ESD protection diodes from the pin to  $V+$  and GND (see Figure 8). To prevent forward biasing these diodes,  $V+$  must be applied before any input signals, and input signal voltages must remain between  $V+$  and GND. If these conditions cannot be guaranteed, then one of the following two protection methods should be employed.

Logic inputs can easily be protected by adding a  $1\text{k}\Omega$  resistor in series with the input (see Figure 8). The resistor limits the input current below the threshold that produces permanent damage, and the sub-microamp input current produces an insignificant voltage drop during normal operation.

Adding a series resistor to the switch input defeats the purpose of using a low  $R_{ON}$  switch, so two small signal diodes can be added in series with the supply pins to provide overvoltage protection for all pins (see Figure 8). These additional diodes limit the analog signal from 1V below  $V+$  to 1V above GND. The low leakage current performance is unaffected by this approach, but the switch resistance may increase, especially at low supply voltages.

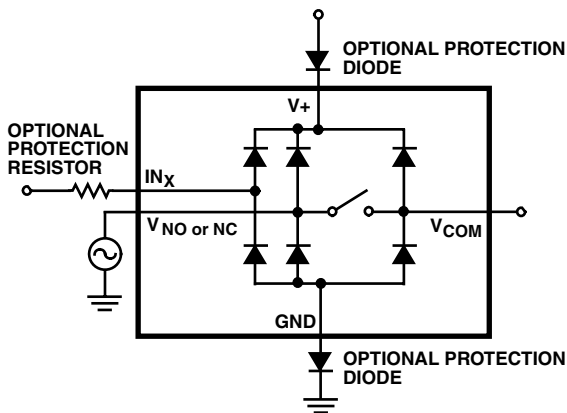


FIGURE 8. OVERVOLTAGE PROTECTION

### Power-Supply Considerations

The ISL512X construction is typical of most CMOS analog switches, except that they have only two supply pins:  $V+$  and GND.  $V+$  and GND drive the internal CMOS switches and set their analog voltage limits. Unlike switches with a 13V maximum supply voltage, the ISL512X 15V maximum supply voltage provides plenty of room for the 10% tolerance of 12V supplies, as well as room for overshoot and noise spikes.

The minimum recommended supply voltage is 2.7V. It is important to note that the input signal range, switching times, and on-resistance degrade at lower supply voltages. Refer to the electrical specification tables and *Typical Performance* curves for details.

$V+$  and GND also power the internal logic and level shifters. The level shifters convert the input logic levels to switched  $V+$  and GND signals to drive the analog switch gate terminals.

This family of switches cannot be operated with bipolar supplies, because the input switching point becomes negative in this configuration.

### Logic-Level Thresholds

This switch family is TTL compatible (0.8V and 2.4V) over a supply range of 3V to 11V (see Figure 15). At 12V the  $V_{IH}$  level is about 2.5V. This is still below the TTL guaranteed high output minimum level of 2.8V, but noise margin is reduced. For best results with a 12V supply, use a logic family that provides a  $V_{OH}$  greater than 3V.

The digital input stages draw supply current whenever the digital input voltage is not at one of the supply rails. Driving the digital input signals from GND to  $V+$  with a fast transition time minimizes power dissipation.

### High-Frequency Performance

In  $50\Omega$  systems, signal response is reasonably flat even past 300MHz (see Figure 16). Figure 16 also illustrates that the frequency response is very consistent over a wide  $V+$  range, and for varying analog signal levels.

An OFF switch acts like a capacitor and passes higher frequencies with less attenuation, resulting in signal feedthrough from a switch's input to its output. Off Isolation is the resistance to this feedthrough, while Crosstalk indicates the amount of feedthrough from one switch to another. Figure 17 details the high Off Isolation and Crosstalk rejection provided by this family. At 10MHz, Off Isolation is about 50dB in  $50\Omega$  systems, decreasing approximately 20dB per decade as frequency increases. Higher load impedances decrease Off Isolation and Crosstalk rejection due to the voltage divider action of the switch OFF impedance and the load impedance.

**Leakage Considerations**

Reverse ESD protection diodes are internally connected between each analog-signal pin and both V+ and GND. One of these diodes conducts if any analog signal exceeds V+ or GND.

Virtually all the analog leakage current comes from the ESD diodes to V+ or GND. Although the ESD diodes on a given signal pin are identical and therefore fairly well balanced, they are reverse biased differently. Each is biased by either

V+ or GND and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the V+ and GND pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity. There is no connection between the analog signal paths and V+ or GND.

**Typical Performance Curves**  $T_A = 25^\circ\text{C}$ , Unless Otherwise Specified

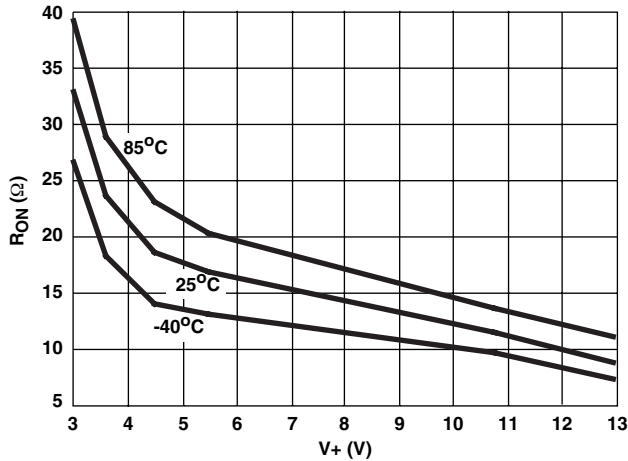


FIGURE 9. ON RESISTANCE vs SUPPLY VOLTAGE

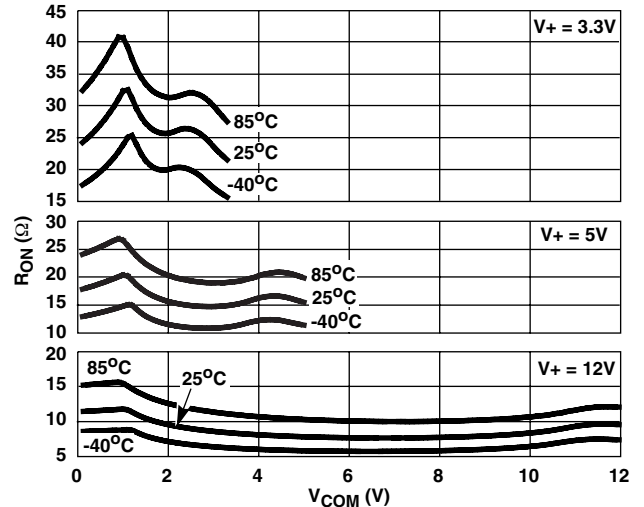


FIGURE 10. ON RESISTANCE vs SWITCH VOLTAGE

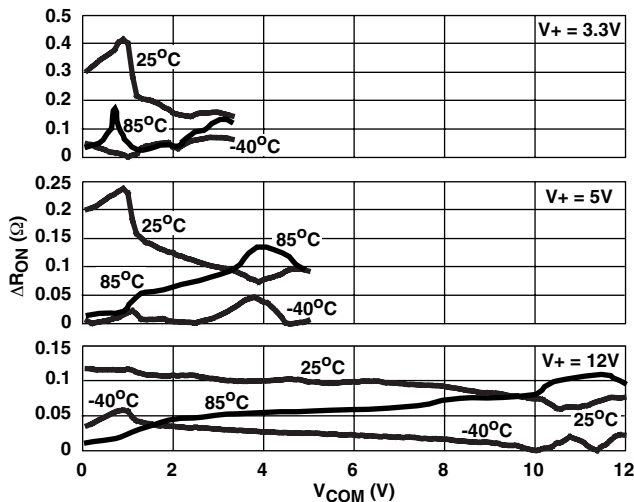


FIGURE 11.  $R_{ON}$  MATCH vs SWITCH VOLTAGE

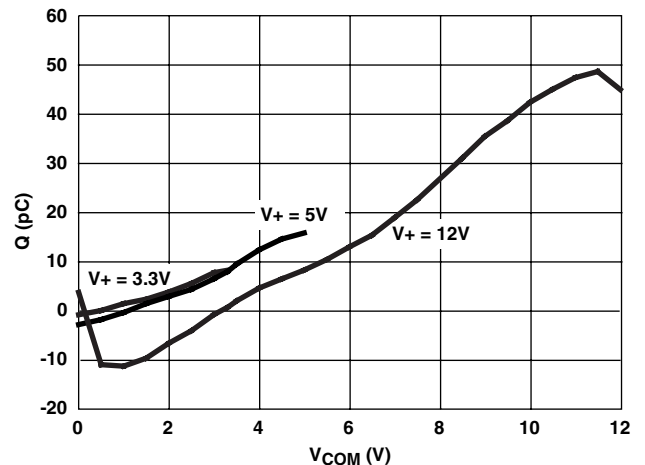


FIGURE 12. CHARGE INJECTION vs SWITCH VOLTAGE

Typical Performance Curves  $T_A = 25^\circ\text{C}$ , Unless Otherwise Specified (Continued)

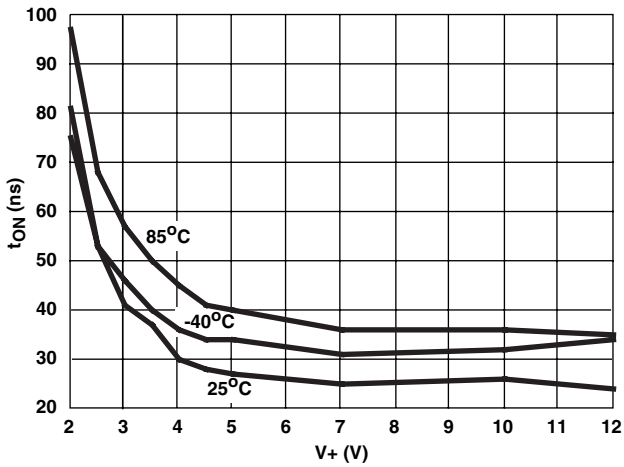


FIGURE 13. TURN - ON TIME vs SUPPLY VOLTAGE

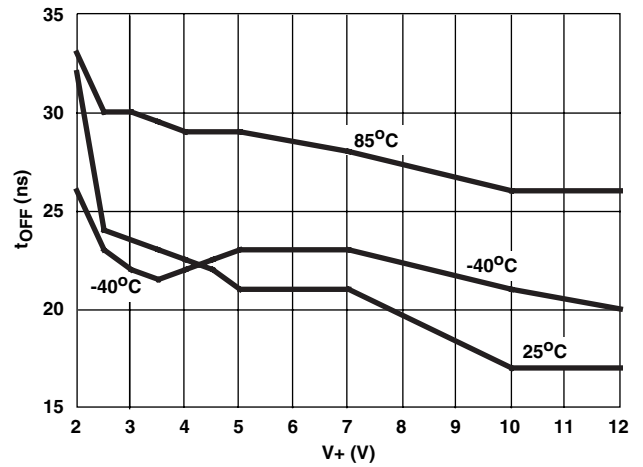


FIGURE 14. TURN - OFF TIME vs SUPPLY VOLTAGE

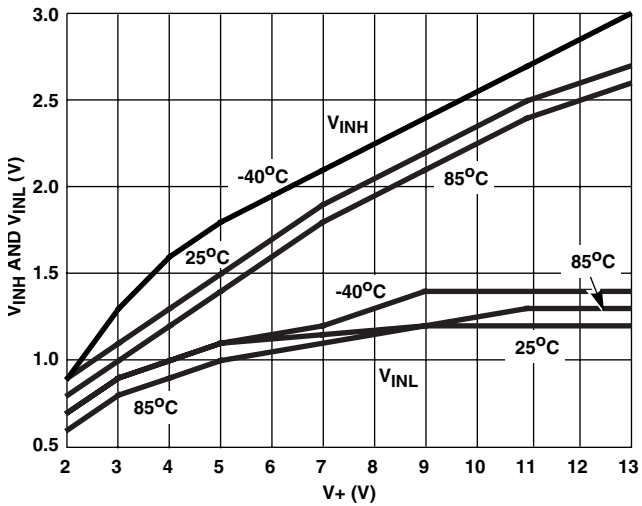


FIGURE 15. DIGITAL SWITCHING POINT vs SUPPLY VOLTAGE

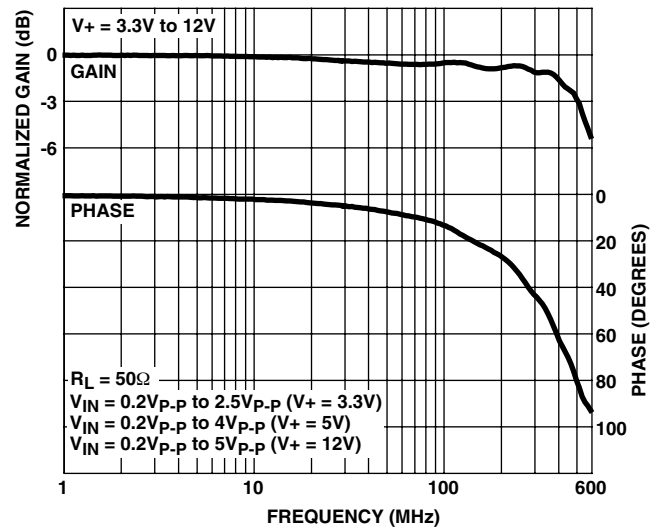


FIGURE 16. FREQUENCY RESPONSE

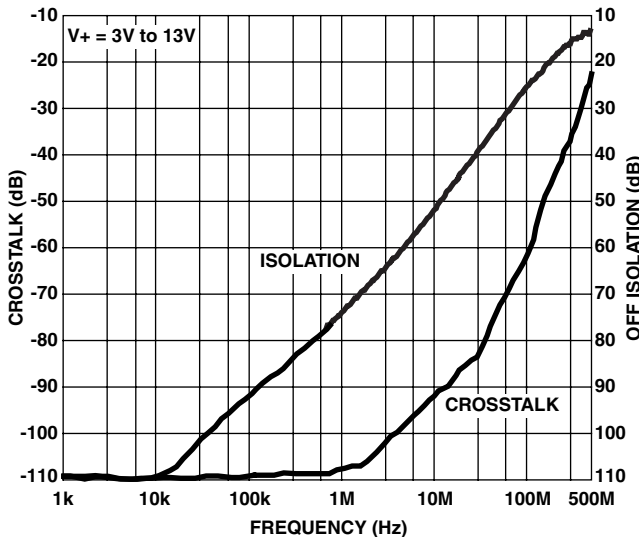


FIGURE 17. CROSSTALK AND OFF ISOLATION

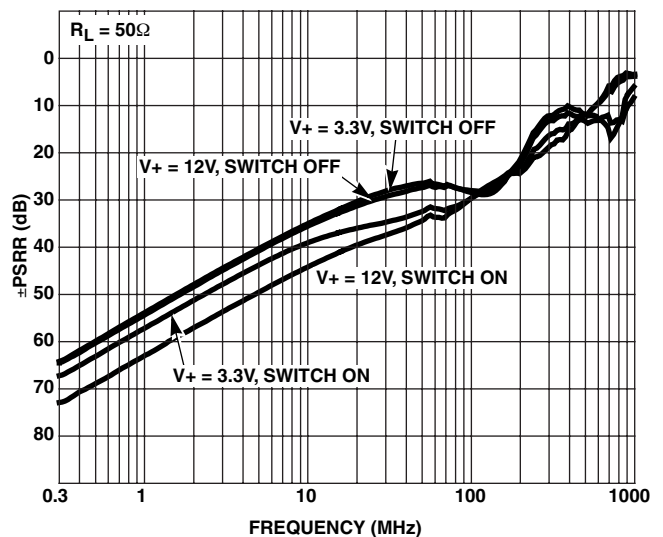


FIGURE 18.  $\pm$ PSRR vs FREQUENCY

## **Die Characteristics**

### **DIE DIMENSIONS:**

ISL512X:  
54 mils x 28 mils (1370 $\mu$ m x 710 $\mu$ m)

### **METALLIZATION:**

Type: Metal 1: AlSi(1%)  
Thickness: Metal 1: 8k $\text{\AA}$   
Type: Metal 2: AlSi (1%)  
Thickness: Metal 2: 10k $\text{\AA}$

### **SUBSTRATE POTENTIAL (POWERED UP):**

GND

### **PASSIVATION:**

Type: Silox  
Thickness: 13k $\text{\AA}$

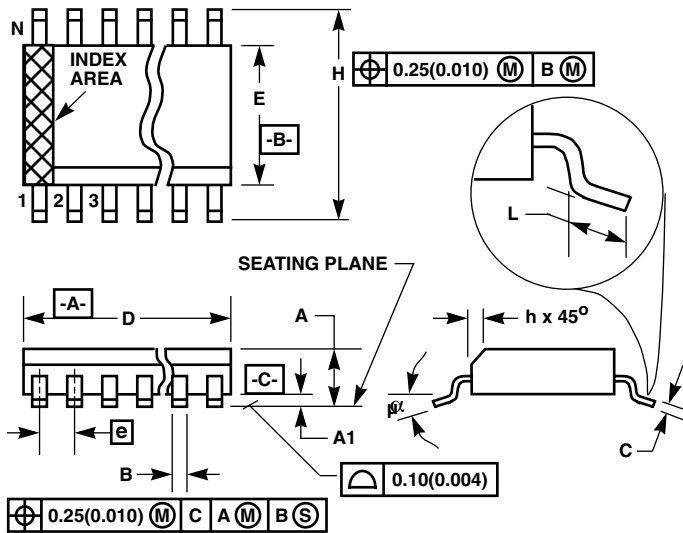
### **TRANSISTOR COUNT:**

ISL5120: 66  
ISL5121: 66  
ISL5122: 66  
ISL5123: 58

### **PROCESS:**

Si Gate CMOS

Small Outline Plastic Packages (SOIC)



**M8.15 (JEDEC MS-012-AA ISSUE C)**  
**8 LEAD NARROW BODY SMALL OUTLINE PLASTIC PACKAGE**

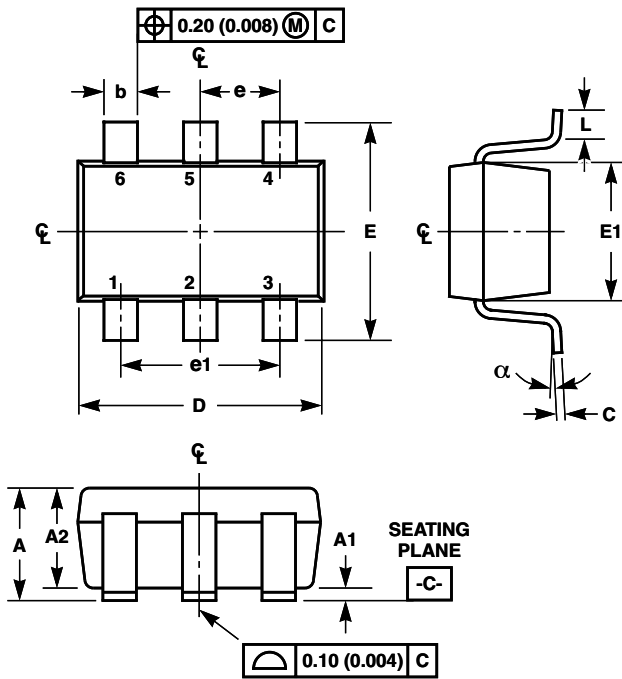
SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.0532	0.0688	1.35	1.75	-
A1	0.0040	0.0098	0.10	0.25	-
B	0.013	0.020	0.33	0.51	9
C	0.0075	0.0098	0.19	0.25	-
D	0.1890	0.1968	4.80	5.00	3
E	0.1497	0.1574	3.80	4.00	4
e	0.050 BSC		1.27 BSC		-
H	0.2284	0.2440	5.80	6.20	-
h	0.0099	0.0196	0.25	0.50	5
L	0.016	0.050	0.40	1.27	6
N	8		8		7
$\alpha$	0°	8°	0°	8°	-

NOTES:

1. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
3. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
4. Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
6. "L" is the length of terminal for soldering to a substrate.
7. "N" is the number of terminal positions.
8. Terminal numbers are shown for reference only.
9. The lead width "B", as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch).
10. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

Rev. 0 12/93

Small Outline Transistor Plastic Packages (SOT23-6)



P6.064

6 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE

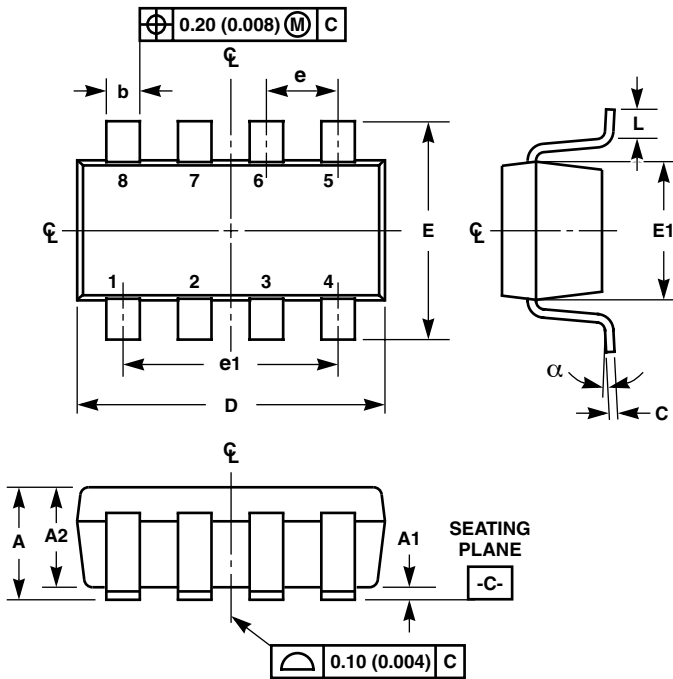
SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.036	0.057	0.90	1.45	-
A1	0.000	0.0059	0.00	0.15	-
A2	0.036	0.051	0.90	1.30	-
b	0.0138	0.0196	0.35	0.50	-
C	0.0036	0.0078	0.09	0.20	-
D	0.111	0.118	2.80	3.00	3
E	0.103	0.118	2.60	3.00	-
E1	0.060	0.068	1.50	1.75	3
e	0.0374 Ref		0.95 Ref		-
e1	0.0748 Ref		1.90 Ref		-
L	0.004	0.023	0.10	0.60	4, 5
N	6		6		6
$\alpha$	0°	10°	0°	10°	-

Rev. 1 2/98

NOTES:

1. Dimensioning and tolerances per ANSI 14.5M-1982.
2. Package conforms to EIAJ SC-74 (1992).
3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.
4. Footlength L measured at reference to seating plane.
5. "L" is the length of flat foot surface for soldering to substrate.
6. "N" is the number of terminal positions.
7. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

**Small Outline Transistor Plastic Packages (SOT23-8)**



**P8.064**

**8 LEAD SMALL OUTLINE TRANSISTOR PLASTIC PACKAGE**

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.036	0.057	0.90	1.45	-
A1	0.000	0.0059	0.00	0.15	-
A2	0.036	0.051	0.90	1.30	-
b	0.011	0.018	0.28	0.45	-
C	0.0036	0.0078	0.09	0.20	-
D	0.111	0.118	2.80	3.00	3
E	0.103	0.118	2.60	3.00	-
E1	0.060	0.068	1.50	1.75	3
e	0.0256 Ref		0.65 Ref		-
e1	0.0768 Ref		1.95 Ref		-
L	0.012	0.020	0.30	0.50	4, 5
N	8		8		6
$\alpha$	0°	10°	0°	10°	-

Rev. 1 10/01

**NOTES:**

1. Dimensioning and tolerances per ANSI 14.5M-1982.
2. Package patterned after EIAJ SC-74 (1992).
3. Dimensions D and E1 are exclusive of mold flash, protrusions, or gate burrs.
4. Footlength L measured at reference to seating plane.
5. "L" is the length of flat foot surface for soldering to substrate.
6. "N" is the number of terminal positions.
7. Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.

All Intersil products are manufactured, assembled and tested utilizing ISO9000 quality systems. Intersil Corporation's quality certifications can be viewed at [www.intersil.com/design/quality](http://www.intersil.com/design/quality)

*Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design, software and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.*

For information regarding Intersil Corporation and its products, see [www.intersil.com](http://www.intersil.com)

**Sales Office Headquarters**

**NORTH AMERICA**  
 Intersil Corporation  
 7585 Irvine Center Drive  
 Suite 100  
 Irvine, CA 92618  
 TEL: (949) 341-7000  
 FAX: (949) 341-7123

Intersil Corporation  
 2401 Palm Bay Rd.  
 Palm Bay, FL 32905  
 TEL: (321) 724-7000  
 FAX: (321) 724-7946

**EUROPE**  
 Intersil Europe Sarl  
 Ave. William Graisse, 3  
 1006 Lausanne  
 Switzerland  
 TEL: +41 21 6140560  
 FAX: +41 21 6140579

**ASIA**  
 Intersil Corporation  
 Unit 1804 18/F Guangdong Water Building  
 83 Austin Road  
 TST, Kowloon Hong Kong  
 TEL: +852 2723 6339  
 FAX: +852 2730 1433